

## Silicon PNP Power Transistors

## 2SA907/908/909

## DESCRIPTION

- With TO-3 package
- Complement to type 2SC1584/1585/1586

## APPLICATIONS

- For power switching and general purpose applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

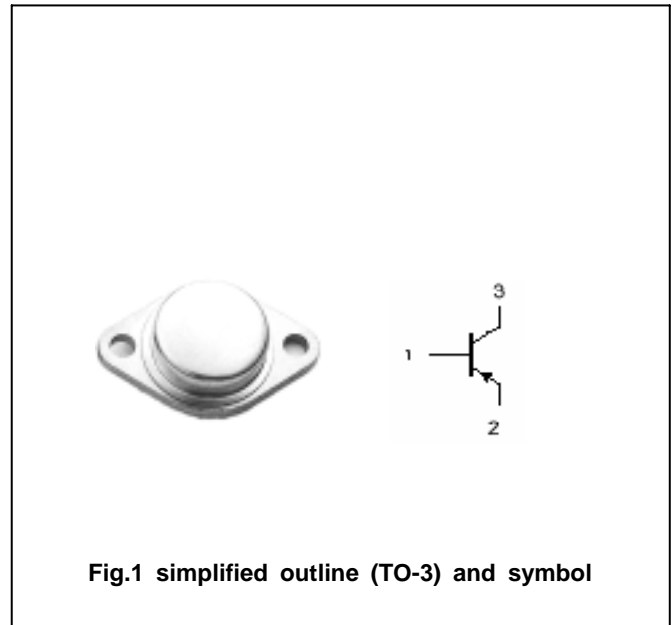


Fig.1 simplified outline (TO-3) and symbol

## Absolute maximum ratings(Ta= )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SA907	-100	V
		2SA908	-150	
		2SA909	-200	
V <sub>CEO</sub>	Collector-emitter voltage	2SA907	-100	V
		2SA908	-150	
		2SA909	-200	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-15	A
I <sub>B</sub>	Base current		-5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	150	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-65~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SA907	I <sub>C</sub> =-50mA ; I <sub>B</sub> =0	-100			V
		2SA908		-150			
		2SA909		-200			
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-10A; I <sub>B</sub> =-1A			-3.0	V
I <sub>CBO</sub>	Collector cut-off current	2SA907	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-1.0	mA
		2SA908	V <sub>CB</sub> =-150V; I <sub>E</sub> =0				
		2SA909	V <sub>CB</sub> =-200V; I <sub>E</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-1.0	mA
h <sub>FE</sub>	DC current gain		I <sub>C</sub> =-5A ; V <sub>CE</sub> =-4V	30			
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-12V		10		MHz

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PACKAGE OUTLINE

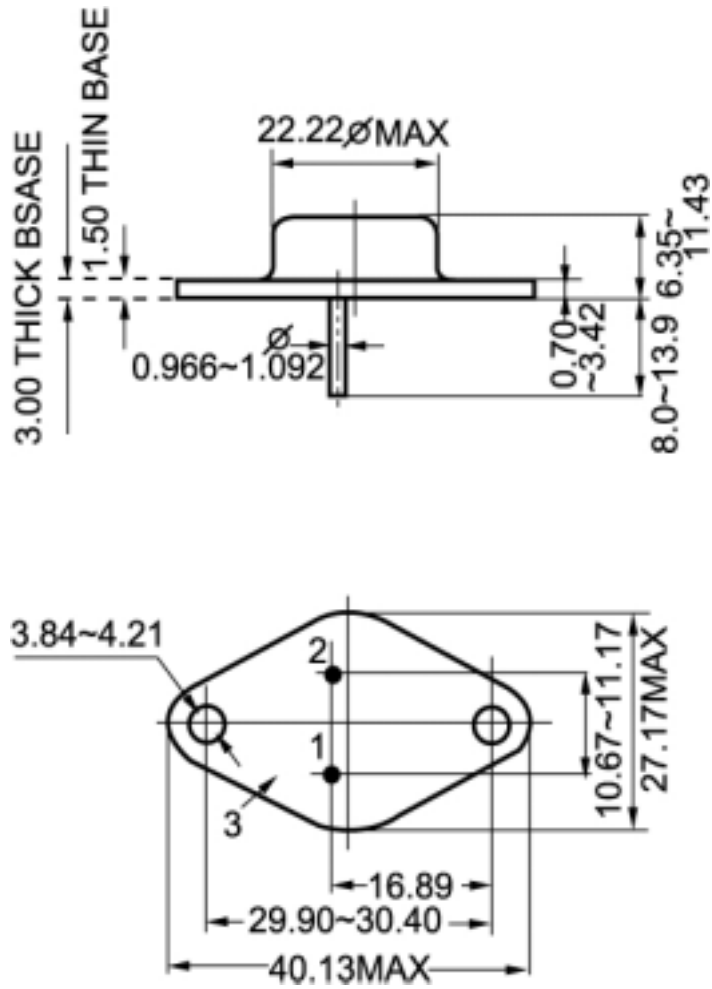


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)